Contents lists available at ScienceDirect

## Synthetic Metals

journal homepage: www.elsevier.com/locate/synmet

## Uniform percolation of inkjet-printed polymer-semiconductor -wrapped carbon nanotube networks by blending with insulating polymer

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#### ARTICLE INFO

Article history: Received 10 February 2016 Received in revised form 2 March 2016 Accepted 7 March 2016 Available online 21 March 2016

Keywords: Carbon nanotube Polymer semiconductor Inkjet-Printing Blending Percolation Thin-film transistor

#### 1. Introduction

Single-walled carbon nanotubes (SWCNTs) are attractive nanomaterials in the development of flexible electronic devices such as optoelectronic devices, chemical and biological sensors, thin-film transistors (TFTs), logic circuits, and computers because of their extraordinary charge carrier mobility, outstanding optical properties in the infrared region, solution processability, and high mechanical flexibility [1–4]. In general, carbon nanotubes are known to form bundles, which alters their intrinsic onedimensional properties and tunable optoelectronic characteristics. Thus, many researchers have focused on isolating individual carbon nanotubes using various techniques. Well-known methods for isolating semiconducting SWCNTs (sc-SWCNTs) involve the sorting of SWCNTs in solution, the removal of metallic SWCNTs (m-SWCNTs) after growth, interactions via surface functional groups, and chemical reactions with SWCNTs. In particular, the solutionbased sorting of sc-SWCNTs via non-covalent functionalization has been demonstrated to be the most promising method for selecting pure sc-SWCNTs without degrading their electrical properties. Among the solution-based sorting methods, which include density gradient ultracentrifugation, column chromatography, partition

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http://dx.doi.org/10.1016/j.synthmet.2016.03.010 0379-6779/© 2016 Elsevier B.V. All rights reserved.

#### ABSTRACT

The enhanced performance uniformity of thin-film transistors (TFTs) fabricated by inkjet printing of polymer-semiconductor-wrapped single-walled carbon nanotube (PSC/SWCNT) networks blended with an insulating polymer binder was investigated. The inkjet-printed PSC/SWCNT network TFTs exhibited varied device performance with a field-effect mobility of  $6.15 \pm 6.75 \text{ cm}^2/\text{V}\cdot\text{s}$ ; the inkjet-printed TFTs fabricated using the poly(methyl methacrylate) (PMMA)-blended PSC/SWCNT layer as a channel exhibited relatively uniform device performance, with a field-effect mobility of  $7.57 \pm 3.32 \text{ cm}^2/\text{V}\cdot\text{s}$ . This notable difference in device performance uniformity is attributed to the blended PMMA, which prevented the PSC/SWCNTs from forming random aggregates and facilitated their uniform percolation when they were inkjet-printed.

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separation, deoxyribonucleic acid wrapping, and conjugated polymer wrapping, the conjugated polymer wrapping method is regarded as a facile route toward the isolation of carbon nanotubes for the large-scale sorting of SWCNTs [5,6]. However, although the resulting conjugated-polymer-semiconductor-wrapped SWCNTs (PSC/SWCNTs) are well-sorted, when the inkjet-printing technique is used to maximize the merits of solution processability of the SWCNTs, the inherently poor jetability of SWCNTs results in randomly percolated PSC/SWCNT networks, which, in turn, leads to variable device performance in the PSC/SWCNT network-based TFTs.

Here, we applied blending systems involving insulating polymer binders to solve the problem of non-uniform performance of PSC/SWCNT TFTs. By introducing the insulating polymers into the PSC/SWCNT network, we improved the uniformity of the performance of inkjet-printed PSC/SWCNT network TFT devices. Our approach enables stable jetability of inks containing PSC/SWCNTs, thereby leading to uniformly percolated PSC/SWCNT network films. The PSC/SWCNT networks blended with the polymer binder resulted in high-performance PSC/SWCNT network-based TFTs with a relatively uniform field-effect mobility of 7.57  $\pm$  3.32 cm<sup>2</sup>/V·s.









Fig. 1. Schematic of transistors and the PSC/SWCNT networks; the chemical structures of F8BT and PMMA used in this study are also shown.

#### 2. Experimental procedure

Fig. 1 shows a schematic of transistors and PSC/SWCNT networks, where poly(9,9-dioctylfluorene-*alt*-benzothiadiazole) (F8BT) was used as a wrapping conjugated polymer [7] and poly (methyl methacrylate) (PMMA) was used as an insulating polymer binder material. The PSC/SWCNT-based TFTs were fabricated in a coplanar (bottom-gate bottom-contact, BGBC) structure, as shown in Fig. 1. For a gate electrode, a 50 nm-thick aluminum layer was thermally evaporated onto the glass substrate and photolitho-graphically patterned. An organic–inorganic hybrid dielectric material composed of siloxane- and zirconium-based compounds ( $\varepsilon_r$  = 3.2) was spun at 3000 rpm for 1 min to form a 1.2  $\mu$ m-thick layer, which was subsequently cured at 200 °C for 2 h. A 50 nm-thick silver layer was then thermally evaporated and photolitho-graphically patterned to form the source/drain contacts with a width and length of 200  $\mu$ m and 20  $\mu$ m, respectively.

Commercially available SWCNTs prepared via a high-pressure carbon monoxide (HiPCO) process (Meijo Nanocarbon) were used for separation and functionalization experiments. The SWCNTs were first dispersed in an  $H_2O$  solution with a 2% (w/v) sodium

cholate surfactant and sonicated; they were subsequently subjected to ultracentrifugation to remove SWCNT bundles and other impurities. The resulting solution contained individually suspended SWCNTs at a final concentration of 0.005% (w/v). In order to obtain an electronically homogeneous sc-SWCNT species, m-SWCNTs were removed from the pristine SWCNTs using a single cascade of the density-induced separation method, as described in the literature [8,9]. Fig. 2(a) shows the radial breathing mode (RBM) results for the Raman spectra of the separated sc-SWCNTs at an excitation energy of 2.41 eV; these results indicate that the m-SWCNTs were removed after separation. Next, a typical dispersion experiment was conducted to prepare the PSC/SWCNTs. Asseparated sc-SWNTs (0.1 mg) and F8BT (10 mg) were suspended in 10 mL of ortho-dichlorobenzene (DCB, purchased from Sigma-Aldrich). The mixture was sonicated in a bath-type sonicator for 10 h to yield a DCB solution of the F8BT-wrapped SWCNTs. A 3 mg/ mL solution prepared by blending the PMMA with 5 wt% of PSC/ SWCNTs was also formulated and mixed for 1 h with continuous stirring to obtain a homogeneous solution. Finally, the prepared solutions were inkjet-printed using a Dimatix printer onto a channel area and annealed at 100 °C for 30 min to evaporate the



Fig. 2. (a) RBM regions in the Raman scattering spectra of the separated sc-SWCNTs; the excitation energy was 2.41 eV. (b) Tapping-mode AFM image of the PSC/SWCNT network blended with the polymer binder. The arrows show the sc-SWCNTs dispersed in the PMMA binder.

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